AMENDMENTS TO THE CLAIMS

1. (Currently amended) A light-emitting device comprising:

a semiconductor excitation light source emitting blue-violet light, and

a solid material illuminant that is made up of a medium that transmits the blue-violet light with low loss and an absorbent for absorbing said blue-violet light, the absorbent containing Sm of 0.01 to 10 mol%, wherein

said solid material illuminant radiates light by inner shell transition of the Sm contained in the absorbent absorbing the blue-violet light, and

said solid material illuminant medium is selected from the group consisting of GaN, AlN, InGaN, InAlN, InGaAlN, Si_3N_4, GaNP, AlNP, InGaNP, InAlNP, InGaAlNP, GaNAs, AlNAs, InGaNAs, InAlNAs, InGaAlNAs, GaNAsP, AlNAsP, InGaNAsP, InAlNAsP, and InGaAlNAsP~~, ZnSe, and ZnSSe~~.

2. (Previously presented) The light-emitting device according to claim 1, wherein

said blue-violet light has a peak wavelength in the range of 398 to 412 nm.

3. (Currently amended) The light-emitting device according to claim 2, wherein

said semiconductor excitation light source emitting blue-violet light is a semiconductor laser device having a narrow spectral line width of lasing.

Claim 4-7 (Canceled).

8. (Previously presented) The light-emitting device according to claim 1, wherein

said solid material illuminant contains a red phosphor having a peak wavelength in the range of 600 to 670 nm, a green phosphor having a peak wavelength in the range of 500 to 550 nm and a blue phosphor having a peak wavelength in the range of 450 to 480 nm.

9. (Previously presented) The light-emitting device according to claim 8, wherein

said red phosphor, said green phosphor and said blue phosphor each contain rare earth elements.

10. (Previously presented) The light-emitting device according to claim 8, wherein

said red phosphor contains at least either Sm or Eu.

11. (Previously Presented) The light-emitting device according to claim 3, wherein

said semiconductor laser device having a narrow spectral line width of lasing has an active layer of an InGaN semiconductor.

12. (Previously Presented) A light-emitting device comprising:

a semiconductor excitation light source emitting blue-violet light, and

a solid material illuminant that is made up of a medium that transmits the blue-violet light with low loss and an absorbent for absorbing said blue-violet light, the absorbent containing Sm of 0.01 to 10 mol%, wherein

said solid material illuminant radiates light by inner shell transition of the Sm contained in the absorbent absorbing the blue-violet light, and

said solid material illuminant medium contains at least one of nitrides of Ga, In, and Al.

13. (Previously Presented) The light-emitting device according to claim 12, wherein

said blue-violet light has a peak wavelength in the range of 398 to 412 nm.

14. (Previously Presented) The light-emitting device according to claim 13, wherein

said semiconductor excitation light source emitting blue-violet light is a semiconductor laser device having a narrow spectral line width of lasing.

15. (Previously Presented) The light-emitting device according to claim 14, wherein said semiconductor laser device having a narrow spectral line width of lasing has an active layer of an InGaN semiconductor.

16. (Previously Presented) The light-emitting device according to claim 12, wherein said solid material illuminant contains a red phosphor having a peak wavelength in the range of 600 to 670 nm, a green phosphor having a peak wavelength in the range of 500 to 550 nm and a blue phosphor having a peak wavelength in the range of 450 to 480 nm.

17. (Previously Presented) The light-emitting device according to claim 15, wherein said red phosphor, said green phosphor and said blue phosphor each contain rare earth elements.

18. (Previously Presented) The light-emitting device according to claim 15, wherein said red phosphor contains at least either Sm or Eu.